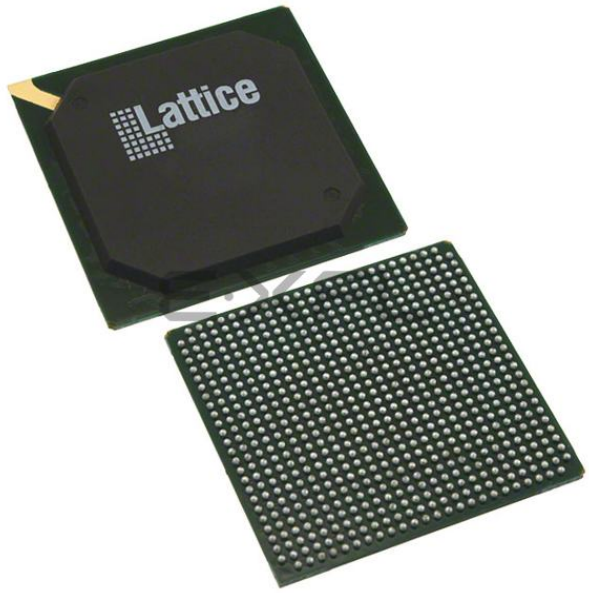
Lattice Semiconductor Corporation - LFE3-70EA-6LFN672I Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	8375
Number of Logic Elements/Cells	67000
Total RAM Bits	4526080
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-70ea-6lfn672i

LatticeECP3 Family Data Sheet Introduction

February 2012 Data Sheet DS1021

Features

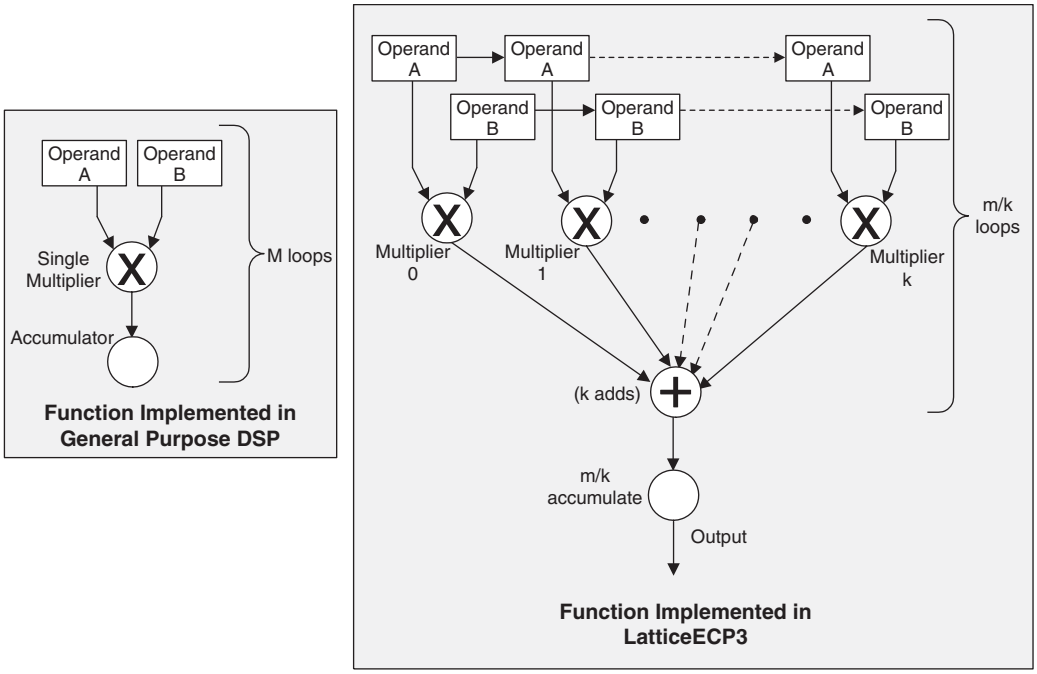
- **Higher Logic Density for Increased System Integration**
  - 17K to 149K LUTs
  - 116 to 586 I/Os
- **Embedded SERDES**
  - 150 Mbps to 3.2 Gbps for Generic 8b10b, 10-bit SERDES, and 8-bit SERDES modes
  - Data Rates 230 Mbps to 3.2 Gbps per channel for all other protocols
  - Up to 16 channels per device: PCI Express, SONET/SDH, Ethernet (1GbE, SGMII, XAUI), CPRI, SMPTE 3G and Serial RapidIO
- **sysDSP™**
  - Fully cascadable slice architecture
  - 12 to 160 slices for high performance multiply and accumulate
  - Powerful 54-bit ALU operations
  - Time Division Multiplexing MAC Sharing
  - Rounding and truncation
  - Each slice supports
    - Half 36x36, two 18x18 or four 9x9 multipliers
    - Advanced 18x36 MAC and 18x18 Multiply-Multiply-Accumulate (MMAC) operations
- **Flexible Memory Resources**
  - Up to 6.85Mbits sysMEM™ Embedded Block RAM (EBR)
  - 36K to 303K bits distributed RAM
- **sysCLOCK Analog PLLs and DLLs**
  - Two DLLs and up to ten PLLs per device
- **Pre-Engineered Source Synchronous I/O**
  - DDR registers in I/O cells
  - Dedicated read/write levelling functionality
  - Dedicated gearing logic
  - Source synchronous standards support
    - ADC/DAC, 7:1 LVDS, XGMII
    - High Speed ADC/DAC devices
  - Dedicated DDR/DDR2/DDR3 memory with DQS support
  - Optional Inter-Symbol Interference (ISI) correction on outputs
- **Programmable sysI/O™ Buffer Supports Wide Range of Interfaces**
  - On-chip termination
  - Optional equalization filter on inputs
  - LVTTL and LVCMOS 33/25/18/15/12
  - SSTL 33/25/18/15 I, II
  - HSTL15 I and HSTL18 I, II
  - PCI and Differential HSTL, SSTL
  - LVDS, Bus-LVDS, LVPECL, RSDS, MLVDS
- **Flexible Device Configuration**
  - Dedicated bank for configuration I/Os
  - SPI boot flash interface
  - Dual-boot images supported
  - Slave SPI
  - TransFR™ I/O for simple field updates
  - Soft Error Detect embedded macro
- **System Level Support**
  - IEEE 1149.1 and IEEE 1532 compliant
  - Reveal Logic Analyzer
  - ORCAstra FPGA configuration utility
  - On-chip oscillator for initialization & general use
  - 1.2 V core power supply

Table 1-1. LatticeECP3™ Family Selection Guide

Device	ECP3-17	ECP3-35	ECP3-70	ECP3-95	ECP3-150
LUTs (K)	17	33	67	92	149
sysMEM Blocks (18 Kbits)	38	72	240	240	372
Embedded Memory (Kbits)	700	1327	4420	4420	6850
Distributed RAM Bits (Kbits)	36	68	145	188	303
18 x 18 Multipliers	24	64	128	128	320
SERDES (Quad)	1	1	3	3	4
PLLs/DLLs	2 / 2	4 / 2	10 / 2	10 / 2	10 / 2
Packages and SERDES Channels/ I/O Combinations					
328 csBGA (10 x 10 mm)	2 / 116				
256 ftBGA (17 x 17 mm)	4 / 133	4 / 133			
484 fpBGA (23 x 23 mm)	4 / 222	4 / 295	4 / 295	4 / 295	
672 fpBGA (27 x 27 mm)		4 / 310	8 / 380	8 / 380	8 / 380
1156 fpBGA (35 x 35 mm)			12 / 490	12 / 490	16 / 586

This allows designers to use highly parallel implementations of DSP functions. Designers can optimize DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2-23 compares the fully serial implementation to the mixed parallel and serial implementation.

Figure 2-23. Comparison of General DSP and LatticeECP3 Approaches



LatticeECP3 sysDSP Slice Architecture Features

The LatticeECP3 sysDSP Slice has been significantly enhanced to provide functions needed for advanced processing applications. These enhancements provide improved flexibility and resource utilization.

The LatticeECP3 sysDSP Slice supports many functions that include the following:

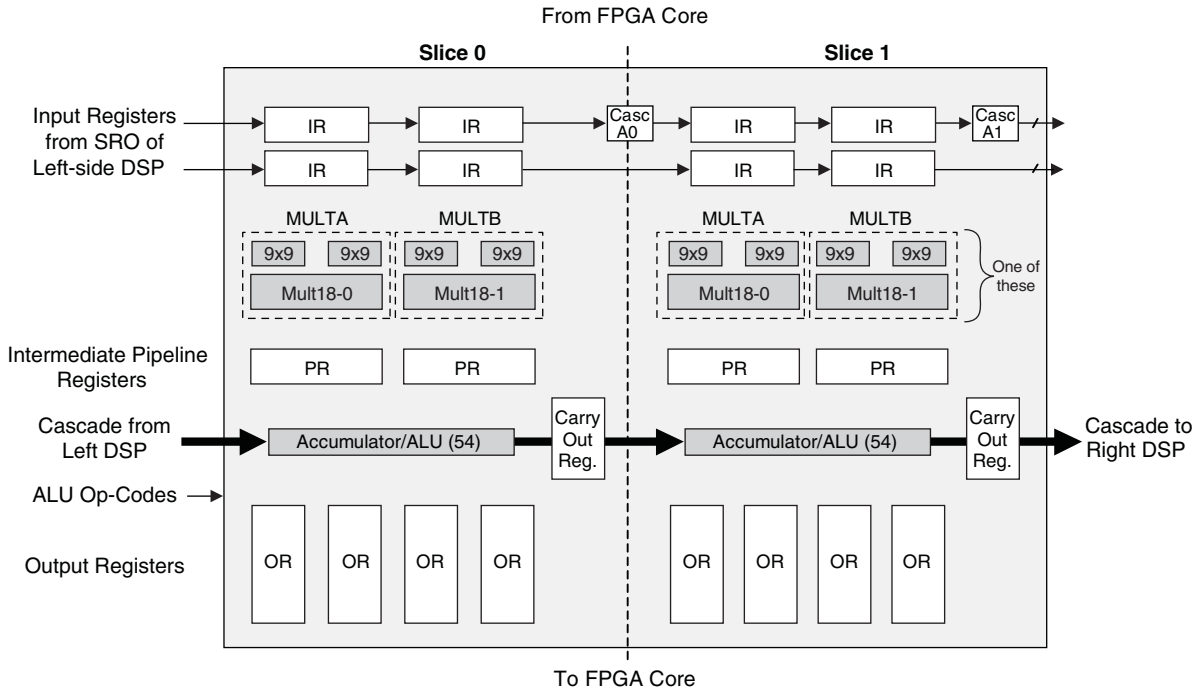
- Multiply (one 18 x 36, two 18 x 18 or four 9 x 9 Multiplies per Slice)
- Multiply (36 x 36 by cascading across two sysDSP slices)
- Multiply Accumulate (up to 18 x 36 Multipliers feeding an Accumulator that can have up to 54-bit resolution)
- Two Multiplies feeding one Accumulate per cycle for increased processing with lower latency (two 18 x 18 Multiplies feed into an accumulator that can accumulate up to 52 bits)
- Flexible saturation and rounding options to satisfy a diverse set of applications situations
- Flexible cascading across DSP slices
  - Minimizes fabric use for common DSP and ALU functions
  - Enables implementation of FIR Filter or similar structures using dedicated sysDSP slice resources only
  - Provides matching pipeline registers
  - Can be configured to continue cascading from one row of sysDSP slices to another for longer cascade chains
- Flexible and Powerful Arithmetic Logic Unit (ALU) Supports:
  - Dynamically selectable ALU OPCODE
  - Ternary arithmetic (addition/subtraction of three inputs)
  - Bit-wise two-input logic operations (AND, OR, NAND, NOR, XOR and XNOR)
  - Eight flexible and programmable ALU flags that can be used for multiple pattern detection scenarios, such

as, overflow, underflow and convergent rounding, etc.
— Flexible cascading across slices to get larger functions

- RTL Synthesis friendly synchronous reset on all registers, while still supporting asynchronous reset for legacy users
- Dynamic MUX selection to allow Time Division Multiplexing (TDM) of resources for applications that require processor-like flexibility that enables different functions for each clock cycle

For most cases, as shown in Figure 2-24, the LatticeECP3 DSP slice is backwards-compatible with the LatticeECP2™ sysDSP block, such that, legacy applications can be targeted to the LatticeECP3 sysDSP slice. The functionality of one LatticeECP2 sysDSP Block can be mapped into two adjacent LatticeECP3 sysDSP slices, as shown in Figure 2-25.

Figure 2-24. Simplified sysDSP Slice Block Diagram



MMAC DSP Element

The LatticeECP3 supports a MAC with two multipliers. This is called Multiply Multiply Accumulate or MMAC. In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value and with the result of the multiplier operation of operands BA and BB. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-28 shows the MMAC sysDSP element.

Figure 2-28. MMAC sysDSP Element

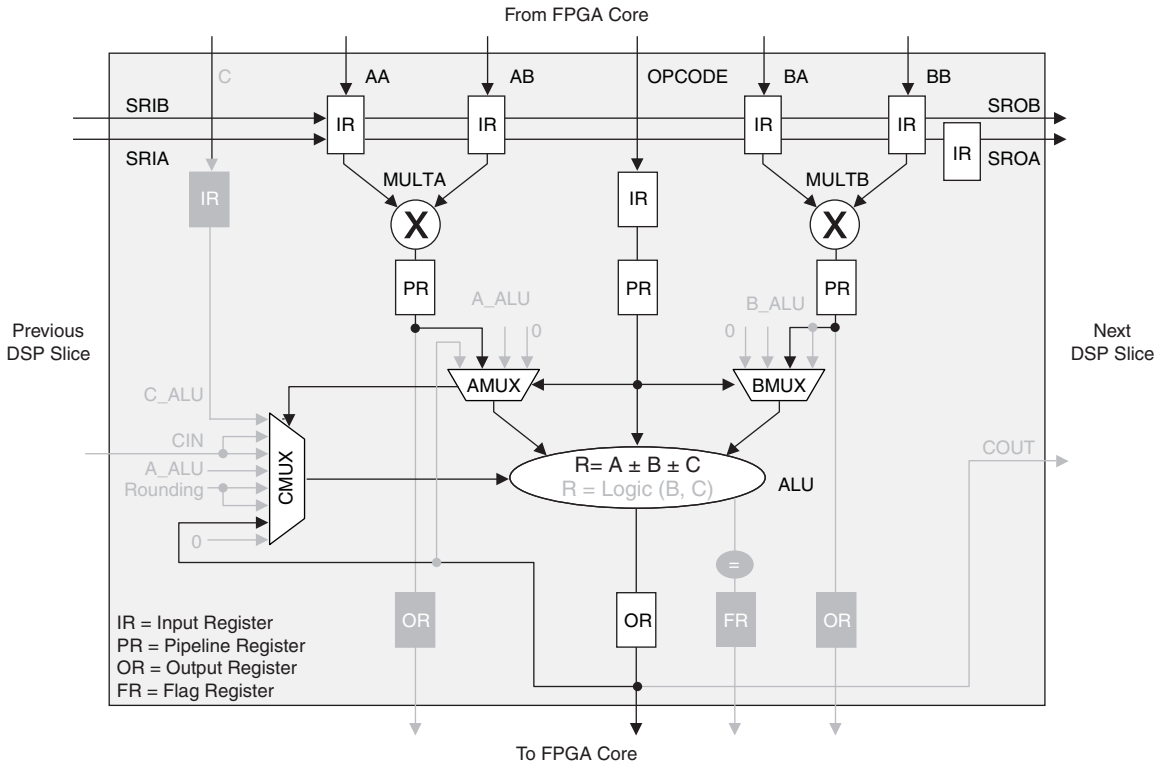
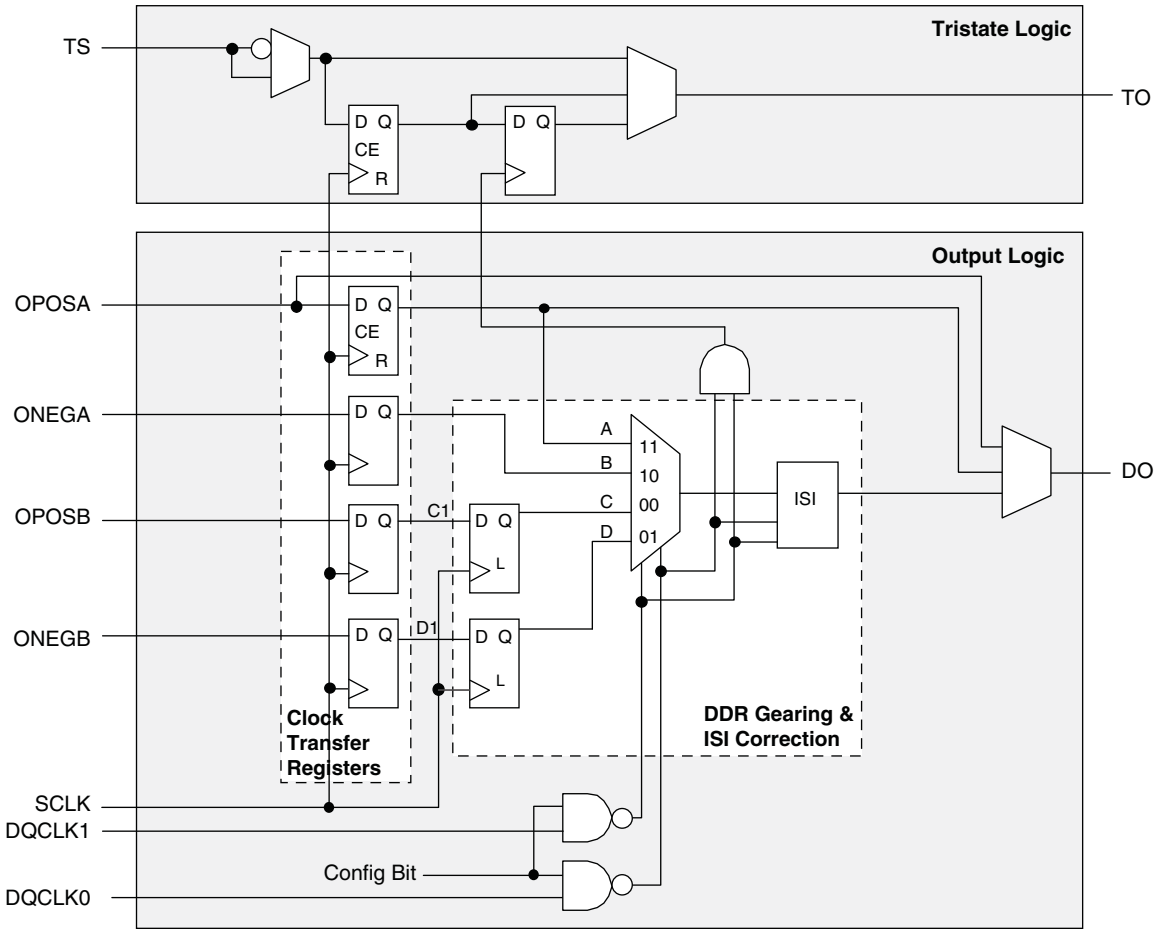


Figure 2-34. Output and Tristate Block for Left and Right Edges



Tristate Register Block

The tristate register block registers tri-state control signals from the core of the device before they are passed to the sysI/O buffers. The block contains a register for SDR operation and an additional register for DDR operation.

In SDR and non-gearing DDR modes, TS input feeds one of the flip-flops that then feeds the output. In DDRX2 mode, the register TS input is fed into another register that is clocked using the DQCLK0 and DQCLK1 signals. The output of this register is used as a tristate control.

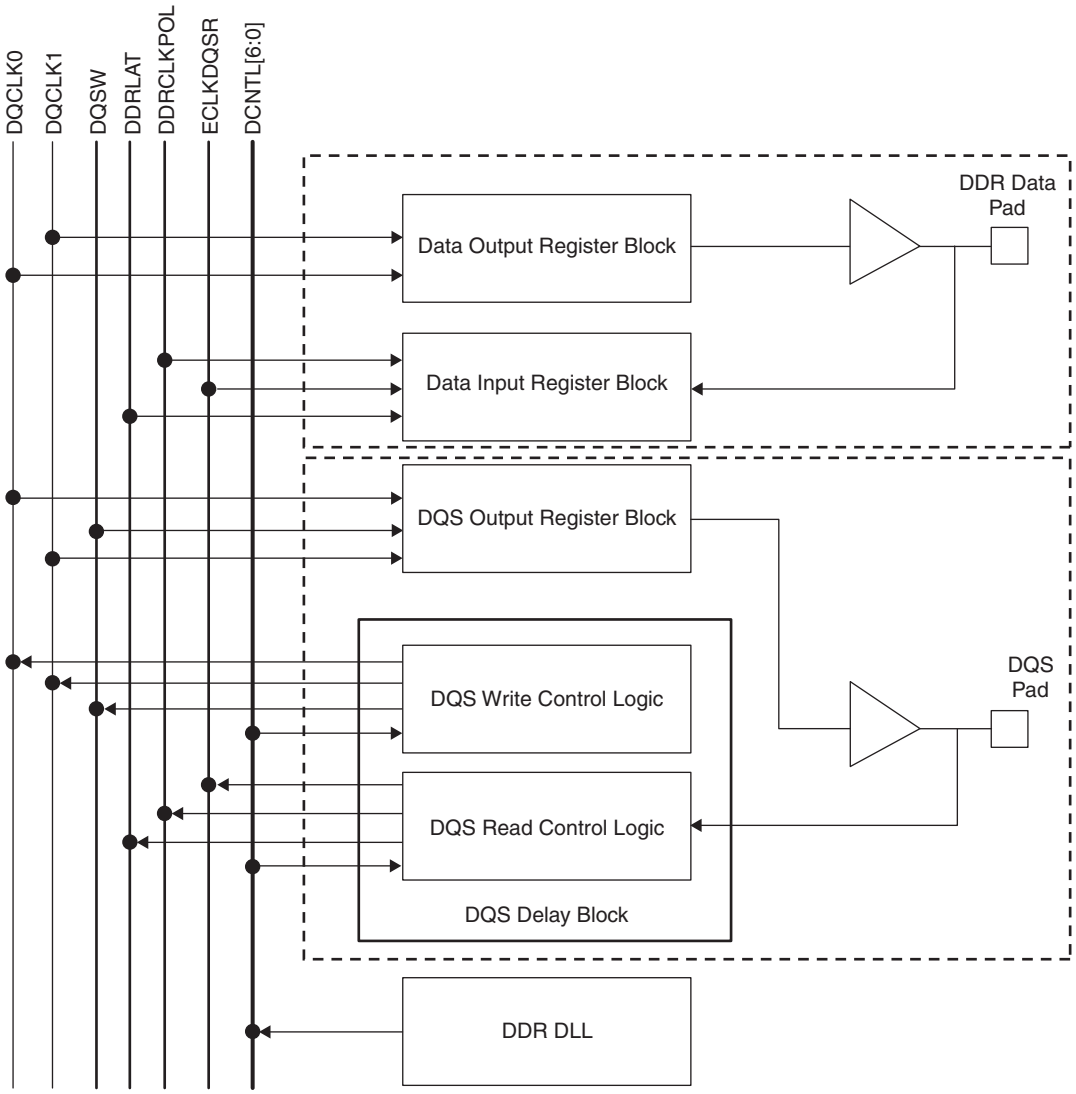
ISI Calibration

The setting for Inter-Symbol Interference (ISI) cancellation occurs in the output register block. ISI correction is only available in the DDRX2 modes. ISI calibration settings exist once per output register block, so each I/O in a DQS-12 group may have a different ISI calibration setting.

The ISI block extends output signals at certain times, as a function of recent signal history. So, if the output pattern consists of a long strings of 0's to long strings of 1's, there are no delays on output signals. However, if there are quick, successive transitions from 010, the block will stretch out the binary 1. This is because the long trail of 0's will cause these symbols to interfere with the logic 1. Likewise, if there are quick, successive transitions from 101, the block will stretch out the binary 0. This block is controlled by a 3-bit delay control that can be set in the DQS control logic block.

For more information about this topic, please see the list of technical documentation at the end of this data sheet.

Figure 2-37. DQS Local Bus



Polarity Control Logic

In a typical DDR Memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the READ cycle) is unknown. The LatticeECP3 family contains dedicated circuits to transfer data between these domains. A clock polarity selector is used to prevent set-up and hold violations at the domain transfer between DQS (delayed) and the system clock. This changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each READ cycle for the correct clock polarity.

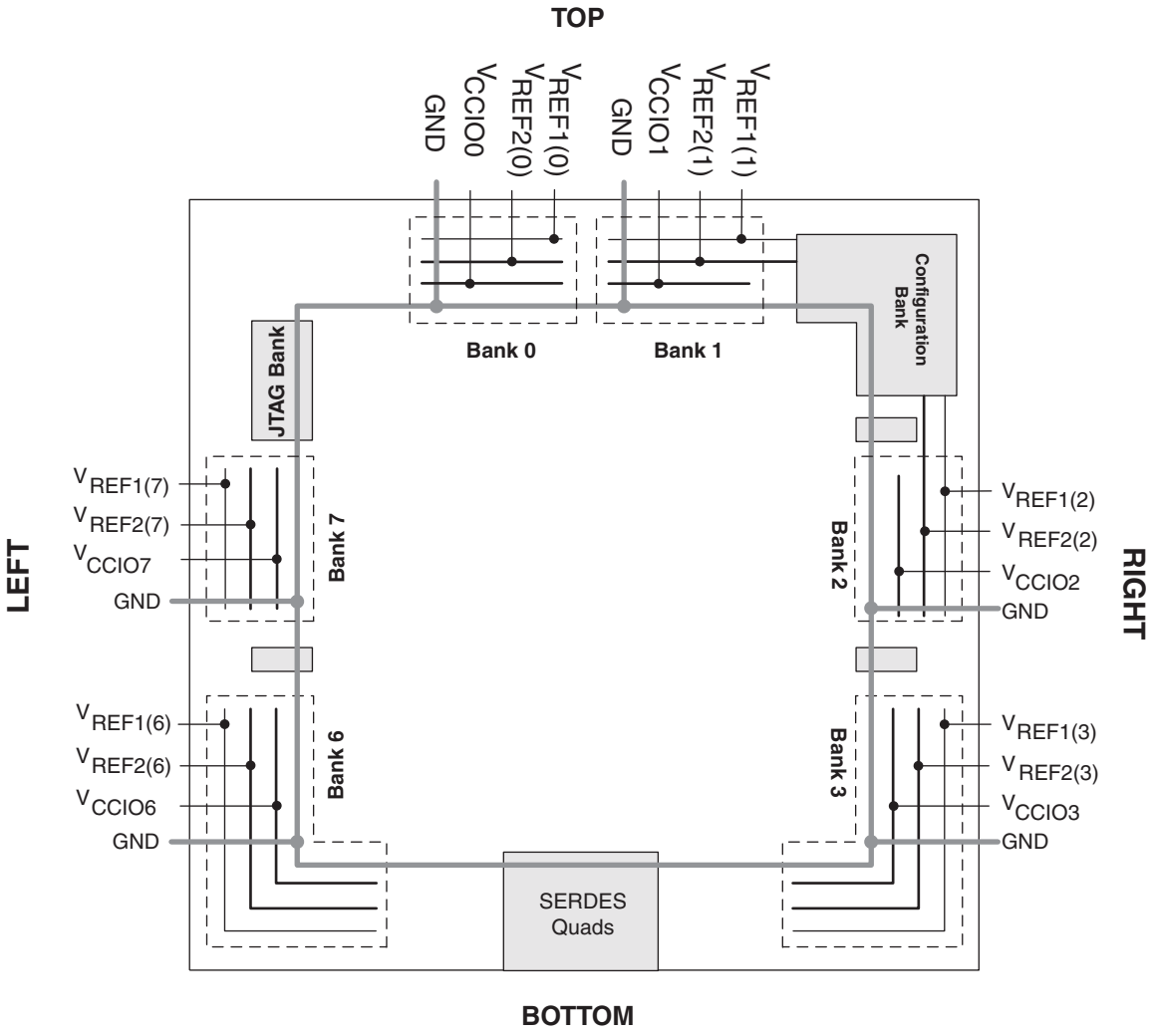
Prior to the READ operation in DDR memories, DQS is in tristate (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit detects the first DQS rising edge after the preamble state. This signal is used to control the polarity of the clock to the synchronizing registers.

DDR3 Memory Support

LatticeECP3 supports the read and write leveling required for DDR3 memory interfaces.

Read leveling is supported by the use of the DDRCLKPOL and the DDRLAT signals generated in the DQS Read Control logic block. These signals dynamically control the capture of the data with respect to the DQS at the input register block.

Figure 2-38. LatticeECP3 Banks



LatticeECP3 devices contain two types of sysI/O buffer pairs.

1. **Top (Bank 0 and Bank 1) and Bottom sysIO Buffer Pairs (Single-Ended Outputs Only)**
   The sysI/O buffer pairs in the top banks of the device consist of two single-ended output drivers and two sets of single-ended input buffers (both ratioed and referenced). One of the referenced input buffers can also be configured as a differential input. Only the top edge buffers have a programmable PCI clamp.

   The two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

   The top and bottom sides are ideal for general purpose I/O, PCI, and inputs for LVDS (LVDS outputs are only allowed on the left and right sides). The top side can be used for the DDR3 ADDR/CMD signals.

   The I/O pins located on the top and bottom sides of the device (labeled PTxxA/B or PBxxA/B) are fully hot socketable. Note that the pads in Banks 3, 6 and 8 are wrapped around the corner of the device. In these banks, only the pads located on the top or bottom of the device are hot socketable. The top and bottom side pads can be identified by the Lattice Diamond tool.

2. **Left and Right (Banks 2, 3, 6 and 7) sysI/O Buffer Pairs (50% Differential and 100% Single-Ended Outputs)**
   The sysI/O buffer pairs in the left and right banks of the device consist of two single-ended output drivers, two sets of single-ended input buffers (both ratioed and referenced) and one differential output driver. One of the referenced input buffers can also be configured as a differential input. In these banks the two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential I/O, and the comp (complementary) pad is associated with the negative side of the differential I/O.

   In addition, programmable on-chip input termination (parallel or differential, static or dynamic) is supported on these sides, which is required for DDR3 interface. However, there is no support for hot-socketing for the I/O pins located on the left and right side of the device as the PCI clamp is always enabled on these pins.

   LVDS, RSDS, PPLVDS and Mini-LVDS differential output drivers are available on 50% of the buffer pairs on the left and right banks.

3. **Configuration Bank sysI/O Buffer Pairs (Single-Ended Outputs, Only on Shared Pins When Not Used by Configuration)**
   The sysI/O buffers in the Configuration Bank consist of ratioed single-ended output drivers and single-ended input buffers. This bank does not support PCI clamp like the other banks on the top, left, and right sides.

   The two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

Programmable PCI clamps are only available on the top banks. PCI clamps are used primarily on inputs and bi-directional pads to reduce ringing on the receiving end.

Typical sysI/O I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when V_{CC}, V_{CCIO8} and V_{CCAUX} have reached satisfactory levels. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user’s responsibility to ensure that all other V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. For more information about controlling the output logic state with valid input logic levels during power-up in LatticeECP3 devices, see the list of technical documentation at the end of this data sheet.

The V_{CC} and V_{CCAUX} supply the power to the FPGA core fabric, whereas the V_{CCIO} supplies power to the I/O buffers. In order to simplify system design while providing consistent and predictable I/O behavior, it is recommended that the I/O buffers be powered-up prior to the FPGA core fabric. V_{CCIO} supplies should be powered-up before or together with the V_{CC} and V_{CCAUX} supplies.

Supported sysI/O Standards

The LatticeECP3 sysI/O buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS, LVTTL and other standards. The buffers support the LVTTL, LVCMOS 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V standards. In the LVCMOS and LVTTL modes, the buffer has individual configuration options for drive strength, slew rates, bus maintenance (weak pull-up, weak pull-down, or a bus-keeper latch) and open drain. Other single-ended standards supported include SSTL and HSTL. Differential standards supported include LVDS, BLVDS, LVPECL, MLVDS, RSDS, Mini-LVDS, PPLVDS (point-to-point LVDS), TRLVDS (Transition Reduced LVDS), differential SSTL and differential HSTL. For further information on utilizing the sysI/O buffer to support a variety of standards please see TN1177, LatticeECP3 sysIO Usage Guide.

Register-to-Register Performance[1, 2, 3]

Function	–8 Timing	Units
18x18 Multiply/Accumulate (Input & Output Registers)	200	MHz
18x18 Multiply-Add/Sub (All Registers)	400	MHz

1. These timing numbers were generated using ispLEVER tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
3. For details on -9 speed grade devices, please contact your Lattice Sales Representative.

Derating Timing Tables

Logic timing provided in the following sections of this data sheet and the Diamond and ispLEVER design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond and ispLEVER design tools can provide logic timing numbers at a particular temperature and voltage.

LatticeECP3 Family Timing Adders[1, 2, 3, 4, 5, 7]

Over Recommended Commercial Operating Conditions

Buffer Type	Description	–8	–7	–6	Units
Input Adjusters					
LVDS25E	LVDS, Emulated, VCCIO = 2.5 V	0.03	–0.01	–0.03	ns
LVDS25	LVDS, VCCIO = 2.5 V	0.03	0.00	–0.04	ns
BLVDS25	BLVDS, Emulated, VCCIO = 2.5 V	0.03	0.00	–0.04	ns
MLVDS25	MLVDS, Emulated, VCCIO = 2.5 V	0.03	0.00	–0.04	ns
RSDS25	RSDS, VCCIO = 2.5 V	0.03	–0.01	–0.03	ns
PPLVDS	Point-to-Point LVDS	0.03	–0.01	–0.03	ns
TRLVDS	Transition-Reduced LVDS	0.03	0.00	–0.04	ns
Mini MLVDS	Mini LVDS	0.03	–0.01	–0.03	ns
LVPECL33	LVPECL, Emulated, VCCIO = 3.3 V	0.17	0.23	0.28	ns
HSTL18_I	HSTL_18 class I, VCCIO = 1.8 V	0.20	0.17	0.13	ns
HSTL18_II	HSTL_18 class II, VCCIO = 1.8 V	0.20	0.17	0.13	ns
HSTL18D_I	Differential HSTL 18 class I	0.20	0.17	0.13	ns
HSTL18D_II	Differential HSTL 18 class II	0.20	0.17	0.13	ns
HSTL15_I	HSTL_15 class I, VCCIO = 1.5 V	0.10	0.12	0.13	ns
HSTL15D_I	Differential HSTL 15 class I	0.10	0.12	0.13	ns
SSTL33_I	SSTL_3 class I, VCCIO = 3.3 V	0.17	0.23	0.28	ns
SSTL33_II	SSTL_3 class II, VCCIO = 3.3 V	0.17	0.23	0.28	ns
SSTL33D_I	Differential SSTL_3 class I	0.17	0.23	0.28	ns
SSTL33D_II	Differential SSTL_3 class II	0.17	0.23	0.28	ns
SSTL25_I	SSTL_2 class I, VCCIO = 2.5 V	0.12	0.14	0.16	ns
SSTL25_II	SSTL_2 class II, VCCIO = 2.5 V	0.12	0.14	0.16	ns
SSTL25D_I	Differential SSTL_2 class I	0.12	0.14	0.16	ns
SSTL25D_II	Differential SSTL_2 class II	0.12	0.14	0.16	ns
SSTL18_I	SSTL_18 class I, VCCIO = 1.8 V	0.08	0.06	0.04	ns
SSTL18_II	SSTL_18 class II, VCCIO = 1.8 V	0.08	0.06	0.04	ns
SSTL18D_I	Differential SSTL_18 class I	0.08	0.06	0.04	ns
SSTL18D_II	Differential SSTL_18 class II	0.08	0.06	0.04	ns
SSTL15	SSTL_15, VCCIO = 1.5 V	0.087	0.059	0.032	ns
SSTL15D	Differential SSTL_15	0.087	0.059	0.032	ns
LVTTL33	LVTTL, VCCIO = 3.3 V	0.07	0.07	0.07	ns
LVCMOS33	LVCMOS, VCCIO = 3.3 V	0.07	0.07	0.07	ns
LVCMOS25	LVCMOS, VCCIO = 2.5 V	0.00	0.00	0.00	ns
LVCMOS18	LVCMOS, VCCIO = 1.8 V	–0.13	–0.13	–0.13	ns
LVCMOS15	LVCMOS, VCCIO = 1.5 V	–0.07	–0.07	–0.07	ns
LVCMOS12	LVCMOS, VCCIO = 1.2 V	–0.20	–0.19	–0.19	ns
PCI33	PCI, VCCIO = 3.3 V	0.07	0.07	0.07	ns
Output Adjusters					
LVDS25E	LVDS, Emulated, VCCIO = 2.5 V	1.02	1.14	1.26	ns
LVDS25	LVDS, VCCIO = 2.5 V	–0.11	–0.07	–0.03	ns
BLVDS25	BLVDS, Emulated, VCCIO = 2.5 V	1.01	1.13	1.25	ns
MLVDS25	MLVDS, Emulated, VCCIO = 2.5 V	1.01	1.13	1.25	ns

SERDES/PCS Block Latency

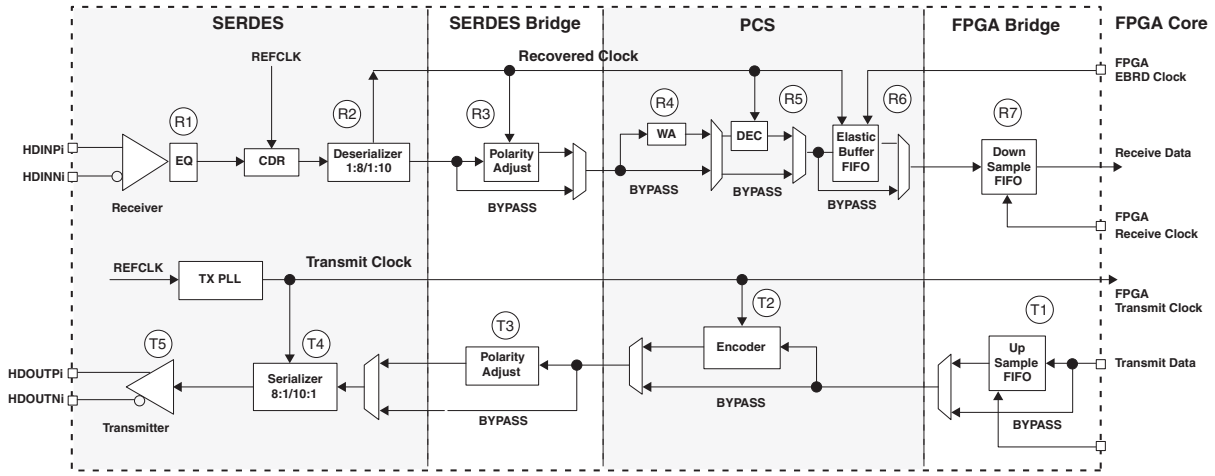
Table 3-8 describes the latency of each functional block in the transmitter and receiver. Latency is given in parallel clock cycles. Figure 3-12 shows the location of each block.

Table 3-8. SERDES/PCS Latency Breakdown

Item	Description	Min.	Avg.	Max.	Fixed	Bypass	Units
Transmit Data Latency[1]							
T1	FPGA Bridge - Gearing disabled with different clocks	1	3	5	—	1	word clk
	FPGA Bridge - Gearing disabled with same clocks	—	—	—	3	1	word clk
	FPGA Bridge - Gearing enabled	1	3	5	—	—	word clk
T2	8b10b Encoder	—	—	—	2	1	word clk
T3	SERDES Bridge transmit	—	—	—	2	1	word clk
T4	Serializer: 8-bit mode	—	—	—	15 + Δ1	—	UI + ps
	Serializer: 10-bit mode	—	—	—	18 + Δ1	—	UI + ps
T5	Pre-emphasis ON	—	—	—	1 + Δ2	—	UI + ps
	Pre-emphasis OFF	—	—	—	0 + Δ3	—	UI + ps
Receive Data Latency[2]							
R1	Equalization ON	—	—	—	Δ1	—	UI + ps
	Equalization OFF	—	—	—	Δ2	—	UI + ps
R2	Deserializer: 8-bit mode	—	—	—	10 + Δ3	—	UI + ps
	Deserializer: 10-bit mode	—	—	—	12 + Δ3	—	UI + ps
R3	SERDES Bridge receive	—	—	—	2	—	word clk
R4	Word alignment	3.1	—	4	—	—	word clk
R5	8b10b decoder	—	—	—	1	—	word clk
R6	Clock Tolerance Compensation	7	15	23	1	1	word clk
R7	FPGA Bridge - Gearing disabled with different clocks	1	3	5	—	1	word clk
	FPGA Bridge - Gearing disabled with same clocks	—	—	—	3	1	word clk
	FPGA Bridge - Gearing enabled	1	3	5	—	—	word clk

1. Δ1 = –245 ps, Δ2 = +88 ps, Δ3 = +112 ps.
2. Δ1 = +118 ps, Δ2 = +132 ps, Δ3 = +700 ps.

Figure 3-12. Transmitter and Receiver Latency Block Diagram



Serial Rapid I/O Type 2/CPRI LV E.24 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-15. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}[1]	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ}[3, 4, 5]	Output data deterministic jitter		—	—	0.17	UI
J_{TX_TJ}[2, 3, 4, 5]	Total output data jitter		—	—	0.35	UI

1. Rise and Fall times measured with board trace, connector and approximately 2.5pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
5. Values are measured at 2.5 Gbps.

Table 3-16. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 2.5 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 2.5 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ}[2, 3, 4, 5]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
J_{RX_RJ}[2, 3, 4, 5]	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
J_{RX_SJ}[2, 3, 4, 5]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
J_{RX_TJ}[1, 2, 3, 4, 5]	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

Gigabit Ethernet/Serial Rapid I/O Type 1/SGMII/CPRI LV E.12 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-17. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ}[3, 4, 5]	Output data deterministic jitter		—	—	0.10	UI
J_{TX_TJ}[2, 3, 4, 5]	Total output data jitter		—	—	0.24	UI

1. Rise and fall times measured with board trace, connector and approximately 2.5 pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
5. Values are measured at 1.25 Gbps.

Table 3-18. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 1.25 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 1.25 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ}[1, 2, 3, 4, 5]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.34	UI
J_{RX_RJ}[1, 2, 3, 4, 5]	Random jitter tolerance (peak-to-peak)		—	—	0.26	UI
J_{RX_SJ}[1, 2, 3, 4, 5]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.11	UI
J_{RX_TJ}[1, 2, 3, 4, 5]	Total jitter tolerance (peak-to-peak)		—	—	0.71	UI
T_{RX_EYE}	Receiver eye opening		0.29	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 1.25 Gbps.

SMPTE SD/HD-SDI/3G-SDI (Serial Digital Interface) Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-19. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR_{SDO}	Serial data rate		270	—	2975	Mbps
$T_{JALIGNMENT}$ [2]	Serial output jitter, alignment	270 Mbps	—	—	0.20	UI
$T_{JALIGNMENT}$ [2]	Serial output jitter, alignment	1485 Mbps	—	—	0.20	UI
$T_{JALIGNMENT}$ [1, 2]	Serial output jitter, alignment	2970Mbps	—	—	0.30	UI
$T_{JTIMING}$	Serial output jitter, timing	270 Mbps	—	—	0.20	UI
$T_{JTIMING}$	Serial output jitter, timing	1485 Mbps	—	—	1.0	UI
$T_{JTIMING}$	Serial output jitter, timing	2970 Mbps	—	—	2.0	UI

Notes:
1. Timing jitter is measured in accordance with SMPTE RP 184-1996, SMPTE RP 192-1996 and the applicable serial data transmission standard, SMPTE 259M-1997 or SMPTE 292M (proposed). A color bar test pattern is used.The value of f_{SCLK} is 270 MHz or 360 MHz for SMPTE 259M, 540 MHz for SMPTE 344M or 1485 MHz for SMPTE 292M serial data rates. See the Timing Jitter Bandpass section.
2. Jitter is defined in accordance with SMPTE RP1 184-1996 as: jitter at an equipment output in the absence of input jitter.
3. All Tx jitter is measured at the output of an industry standard cable driver; connection to the cable driver is via a 50 Ohm impedance differential signal from the Lattice SERDES device.
4. The cable driver drives: RL=75 Ohm, AC-coupled at 270, 1485, or 2970 Mbps, RREFLVL=RREFPRE=4.75 kOhm 1%.

Table 3-20. Receive

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR_{SDI}	Serial input data rate		270	—	2970	Mbps
CID	Stream of non-transitions (=Consecutive Identical Digits)		7(3G)/26(SMPTE Triple rates) @ 10-12 BER	—	—	Bits

Table 3-21. Reference Clock

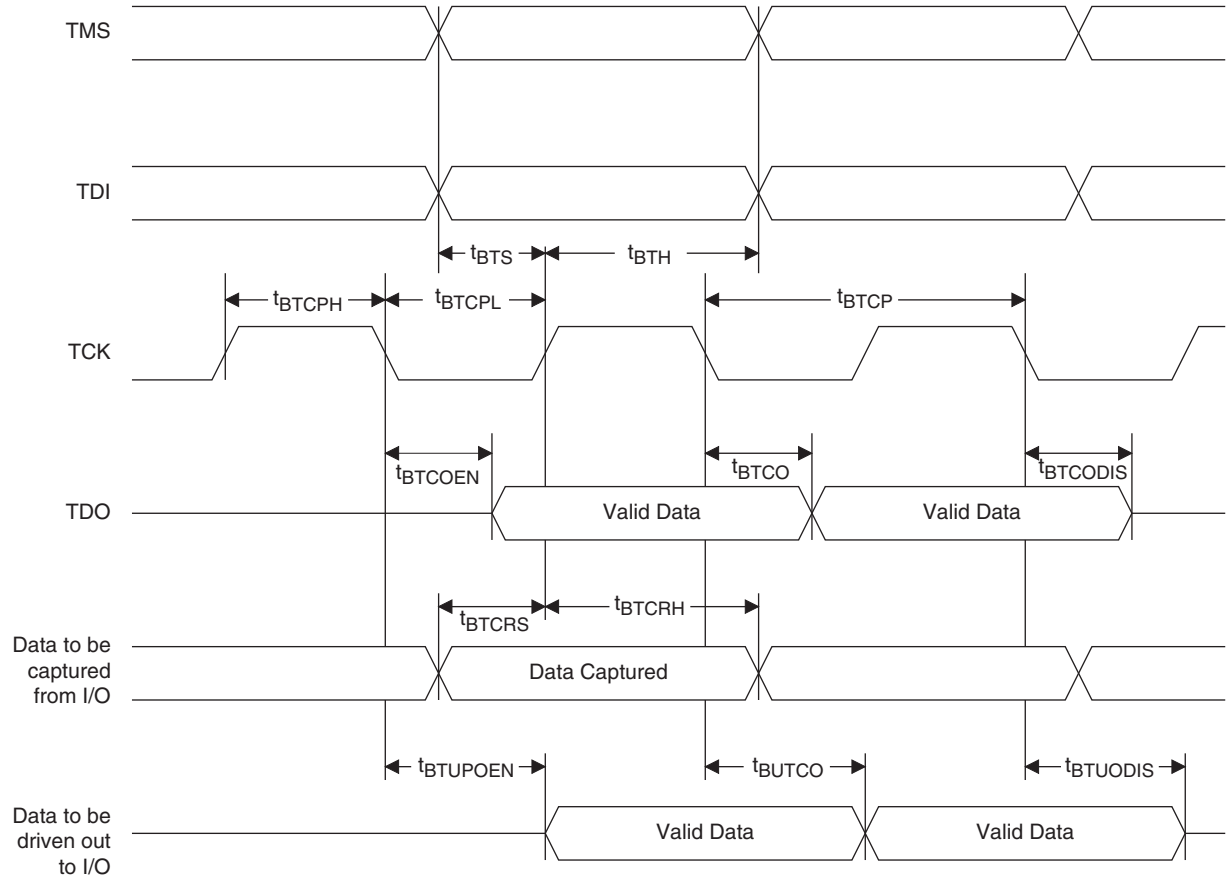
Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
F_{VCLK}	Video output clock frequency		27	—	74.25	MHz
DC_V	Duty cycle, video clock		45	50	55	%

JTAG Port Timing Specifications

Over Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCP}	TCK [BSCAN] clock pulse width	40	—	ns
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTRF}	TCK [BSCAN] rise/fall time	50	—	mV/ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	25	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

Figure 3-32. JTAG Port Timing Waveforms



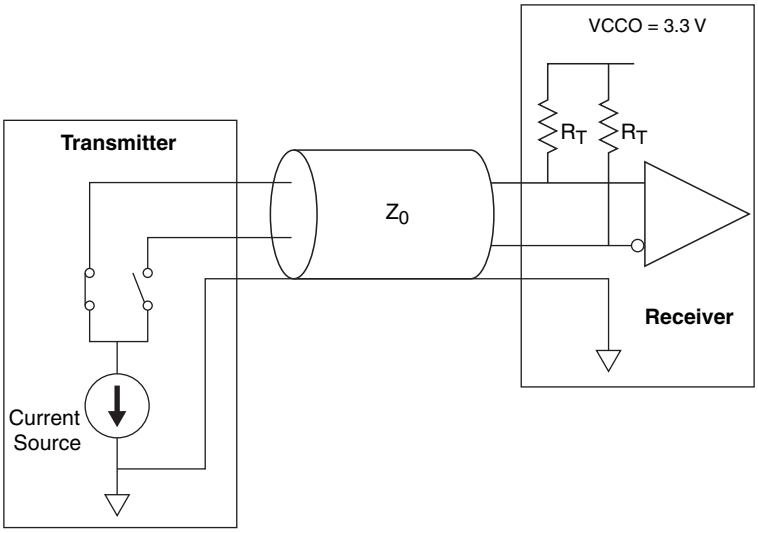
sysI/O Differential Electrical Characteristics

Transition Reduced LVDS (TRLVDS DC Specification)

Over Recommended Operating Conditions

Symbol	Description	Min.	Nom.	Max.	Units
V_{CCO}	Driver supply voltage (+/– 5%)	3.14	3.3	3.47	V
V_{ID}	Input differential voltage	150	—	1200	mV
V_{ICM}	Input common mode voltage	3	—	3.265	V
V_{CCO}	Termination supply voltage	3.14	3.3	3.47	V
R_T	Termination resistance (off-chip)	45	50	55	Ohms

Note: LatticeECP3 only supports the TRLVDS receiver.



Mini LVDS

Over Recommended Operating Conditions

Parameter Symbol	Description	Min.	Typ.	Max.	Units
Z_O	Single-ended PCB trace impedance	30	50	75	Ohms
R_T	Differential termination resistance	50	100	150	Ohms
V_{OD}	Output voltage, differential, $\|V_{OP} - V_{OM}\|$	300	—	600	mV
V_{OS}	Output voltage, common mode, $\|V_{OP} + V_{OM}\|/2$	1	1.2	1.4	V
ΔV_{OD}	Change in V_{OD}, between H and L	—	—	50	mV
ΔV_{ID}	Change in V_{OS}, between H and L	—	—	50	mV
V_{THD}	Input voltage, differential, $\|V_{INP} - V_{INM}\|$	200	—	600	mV
V_{CM}	Input voltage, common mode, $\|V_{INP} + V_{INM}\|/2$	$0.3+(V_{THD}/2)$	—	$2.1-(V_{THD}/2)$	
T_R, T_F	Output rise and fall times, 20% to 80%	—	—	550	ps
T_{ODUTY}	Output clock duty cycle	40	—	60	%

Note: Data is for 6 mA differential current drive. Other differential driver current options are available.

Signal Descriptions (Cont.)

Signal Name	I/O	Description
D7/SPID0	I/O	Parallel configuration I/O. SPI/SPIm data input. Open drain during configuration.
DI/CSSPI0N/CEN	I/O	Serial data input for slave serial mode. SPI/SPIm mode chip select.
Dedicated SERDES Signals[3]		
PCS[Index]_HDINNm	I	High-speed input, negative channel m
PCS[Index]_HDOUTNm	O	High-speed output, negative channel m
PCS[Index]_REFCLKN	I	Negative Reference Clock Input
PCS[Index]_HDINPm	I	High-speed input, positive channel m
PCS[Index]_HDOUTPm	O	High-speed output, positive channel m
PCS[Index]_REFCLKP	I	Positive Reference Clock Input
PCS[Index]_VCCOBm	—	Output buffer power supply, channel m (1.2V/1.5)
PCS[Index]_VCCIBm	—	Input buffer power supply, channel m (1.2V/1.5V)

1. When placing switching I/Os around these critical pins that are designed to supply the device with the proper reference or supply voltage, care must be given.
2. These pins are dedicated inputs or can be used as general purpose I/O.
3. m defines the associated channel in the quad.

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-17EA			ECP3-35EA		
Pin Type		256 ftBGA	328 csBGA	484 fpBGA	256 ftBGA	484 fpBGA	672 fpBGA
Emulated Differential I/O per Bank	Bank 0	13	10	18	13	21	24
	Bank 1	7	5	12	7	18	18
	Bank 2	2	2	4	1	8	8
	Bank 3	4	2	13	5	20	19
	Bank 6	5	1	13	6	22	20
	Bank 7	6	9	10	6	11	13
	Bank 8	12	12	12	12	12	12
Highspeed Differential I/O per Bank	Bank 0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0
	Bank 2	2	2	3	3	6	6
	Bank 3	5	4	9	4	9	12
	Bank 6	5	4	9	4	11	12
	Bank 7	5	6	8	5	9	10
	Bank 8	0	0	0	0	0	0
Total Single Ended/ Total Differential I/O per Bank	Bank 0	26/13	20/10	36/18	26/13	42/21	48/24
	Bank 1	14/7	10/5	24/12	14/7	36/18	36/18
	Bank 2	8/4	9/4	14/7	8/4	28/14	28/14
	Bank 3	18/9	12/6	44/22	18/9	58/29	63/31
	Bank 6	20/10	11/5	44/22	20/10	67/33	65/32
	Bank 7	23/11	30/15	36/18	23/11	40/20	46/23
	Bank 8	24/12	24/12	24/12	24/12	24/12	24/12
DDR Groups Bonded per Bank[2]	Bank 0	2	1	3	2	3	4
	Bank 1	1	0	2	1	3	3
	Bank 2	0	0	1	0	2	2
	Bank 3	1	0	3	1	3	4
	Bank 6	1	0	3	1	4	4
	Bank 7	1	2	2	1	3	3
	Configuration Bank 8	0	0	0	0	0	0
SERDES Quads		1	1	1	1	1	1

1. These pins must remain floating on the board.
2. Some DQS groups may not support DQS-12. Refer to the device pinout (.csv) file.

Package Pinout Information

Package pinout information can be found under “Data Sheets” on the LatticeECP3 product pages on the Lattice website at http://www.latticesemi.com/Products/FPGAandCPLD/LatticeECP3 and in the Diamond or ispLEVER software tools. To create pinout information from within ispLEVER Design Planner, select **Tools > Spreadsheet View**. Then select **Select File > Export** and choose a type of output file. To create a pin information file from within Diamond select **Tools > Spreadsheet View** or **Tools >Package View**; then, select **File > Export** and choose a type of output file. See Diamond or ispLEVER Help for more information.

Thermal Management

Thermal management is recommended as part of any sound FPGA design methodology. To assess the thermal characteristics of a system, Lattice specifies a maximum allowable junction temperature in all device data sheets. Designers must complete a thermal analysis of their specific design to ensure that the device and package do not exceed the junction temperature limits. Refer to the Thermal Management document to find the device/package specific thermal values.

For Further Information

For further information regarding Thermal Management, refer to the following:

- Thermal Management document
- TN1181, Power Consumption and Management for LatticeECP3 Devices
- Power Calculator tool included with the Diamond and ispLEVER design tools, or as a standalone download from www.latticesemi.com/software

LatticeECP3 Family Data Sheet Revision History

March 2015 **Data Sheet DS1021**

Date	Version	Section	Change Summary
March 2015	2.8EA	Pinout Information All	Updated Package Pinout Information section. Changed reference to http://www.latticesemi.com/Products/FPGAandCPLD/LatticeECP3.
			Minor style/formatting changes.
April 2014	02.7EA	DC and Switching Characteristics	Updated LatticeECP3 Supply Current (Standby) table power numbers.
			Removed speed grade -9 timing numbers in the following sections: — Typical Building Block Function Performance — LatticeECP3 External Switching Characteristics — LatticeECP3 Internal Switching Characteristics — LatticeECP3 Family Timing Adders
		Ordering Information	Removed ordering information for -9 speed grade devices.
March 2014	02.6EA	DC and Switching Characteristics	Added information to the sysI/O Single-Ended DC Electrical Characteristics section footnote.
February 2014	02.5EA	DC and Switching Characteristics	Updated Hot Socketing Specifications table. Changed I_{PW} to I_{PD} in footnote 3.
			Updated the following figures: — Figure 3-25, sysCONFIG Port Timing — Figure 3-27, Wake-Up Timing
		Supplemental Information	Added technical note references.
September 2013	02.4EA	DC and Switching Characteristics	Updated the Wake-Up Timing Diagram
			Added the following figures: — Master SPI POR Waveforms — SPI Configuration Waveforms — Slave SPI HOLDN Waveforms
			Added tIODISS and tIOENSS parameters in LatticeECP3 sysCONFIG Port Timing Specifications table.
June 2013	02.3EA	Architecture	sysI/O Buffer Banks text section – Updated description of “Top (Bank 0 and Bank 1) and Bottom sysIO Buffer Pairs (Single-Ended Outputs Only)” for hot socketing information.
			sysI/O Buffer Banks text section – Updated description of “Configuration Bank sysI/O Buffer Pairs (Single-Ended Outputs, Only on Shared Pins When Not Used by Configuration)” for PCI clamp information.
			On-Chip Oscillator section – clarified the speed of the internal CMOS oscillator (130 MHz +/- 15%).
			Architecture Overview section – Added information on the state of the register on power up and after configuration.
		DC and Switching Characteristics	sysI/O Recommended Operating Conditions table – Removed reference to footnote 1 from RSDS standard.
			sysI/O Single-Ended DC Electrical Characteristics table – Modified footnote 1.
			Added Oscillator Output Frequency table.
			LatticeECP3 sysCONFIG Port Timing Specifications table – Updated min. column for t_{CODO} parameter.
			LatticeECP3 Family Timing Adders table – Description column, references to VCCIO = 3.0V changed to 3.3V. For PPLVDS, description changed from emulated to True LVDS and VCCIO = 2.5V changed to VCCIO = 2.5V or 3.3V.